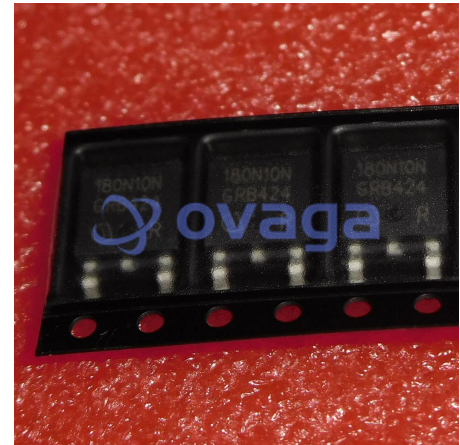


MOSFET N-Channel MOSFET 20-200V

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-252
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPD180N10N3G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPD180N10N3G is a power MOSFET transistor designed and manufactured by Infineon Technologies. Here are some of its features:

Features

Drain-source voltage (V_{dss}): 100V

Continuous drain current (I_d): 180A

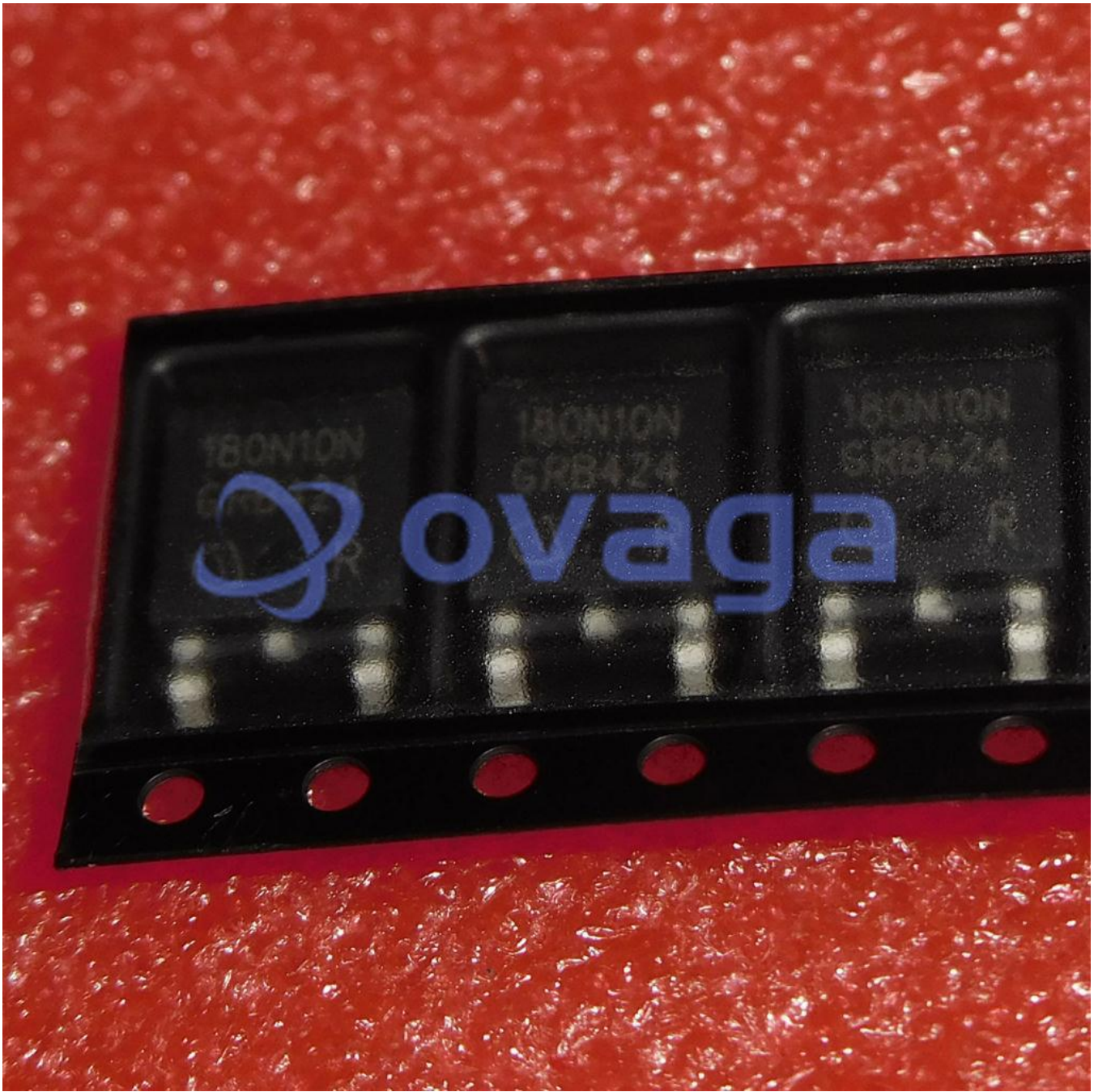
Maximum on-state resistance (R_{ds(on)}): 3.3mΩ

Gate charge (Q_g): 270nC

Fast switching and low switching losses

High current handling capability

RoHS compliant



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



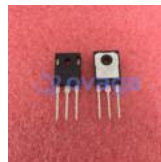
[IPB180N06S4-H1](#)

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PG-TO263-7-3



[IPG20N04S4-12](#)

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TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation
TO-247



[IPD25N06S4L-30](#)

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PG-TO252-3



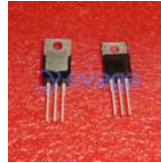
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[IPD70R1K4P7S](#)

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[IPP120P04P4L-03](#)

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